



# **SiPM timing measurements at LAL**

**XII SuperB Workshop  
Frascati, September 27-31 2010**

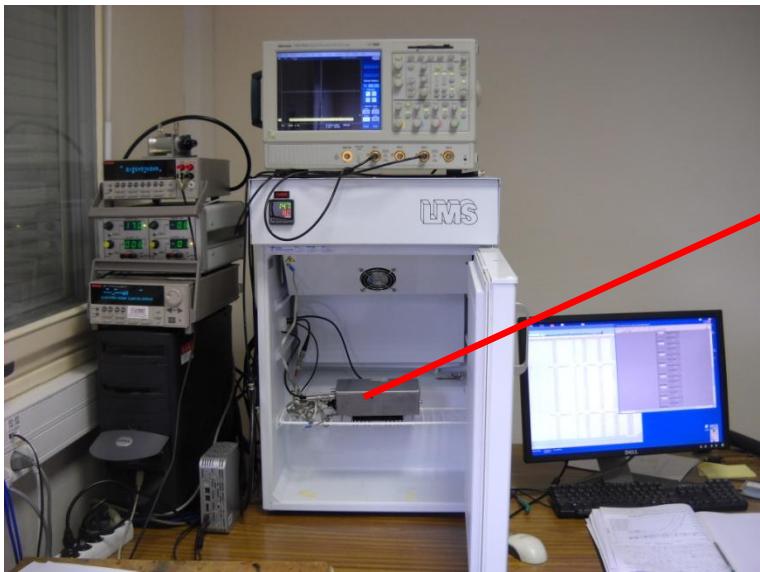
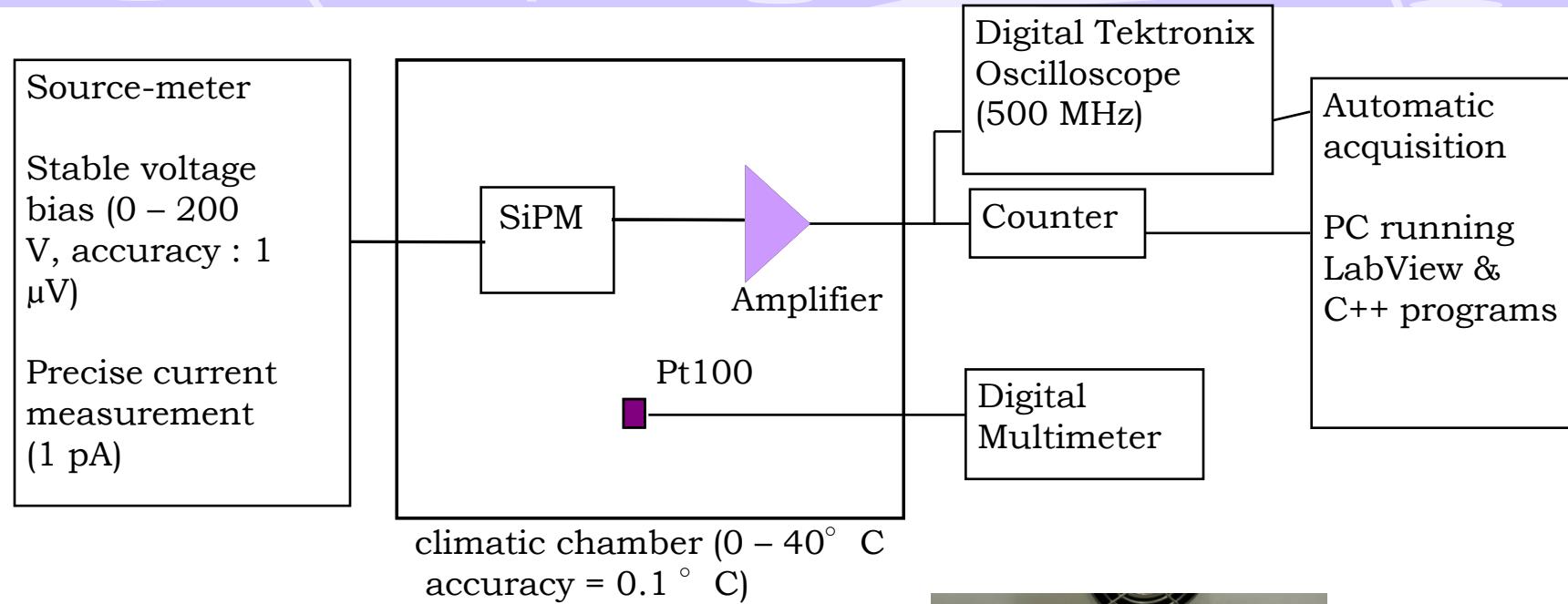
Véronique Puill

C. Bazin, D. Breton, L. Burmistrov, V. Chaumat, N. Dinu,  
J. Maalmi, A. Stocchi, Jean-François Vagnucci

# SiPMs (1 mm<sup>2</sup>) measured at LAL

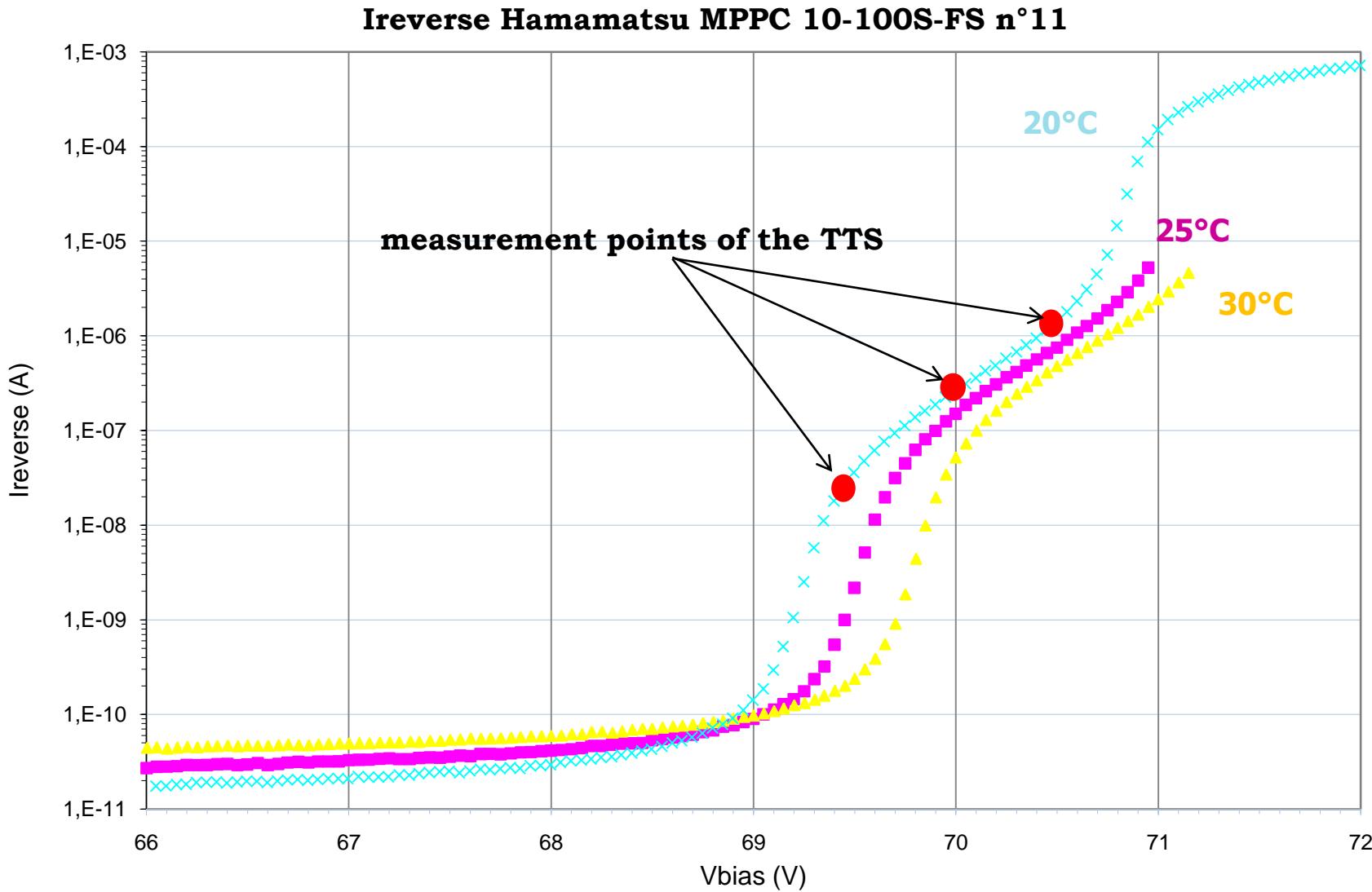
	Reference	Pixel nb	Pixel size (μm)	Fill factor (%)
<b>F.B.K B</b>	<b>B11</b>	400	<b>50 x 50</b>	
	<b>B13</b>	400	<b>50 x 50</b>	
<b>Hamamatsu MPPC</b>	<b>S10362-11-25</b>	1600	<b>25 x 25</b>	<b>31</b>
	<b>S10362-11-50</b>	400	<b>50 x 50</b>	<b>61.6</b>
	<b>S10362-11-100</b>	100	<b>100 x 100</b>	<b>78.5</b>
	<b>10-50S-BK 4S</b>	400	<b>50 x 50</b>	<b>38</b>
	<b>10-100S-FS</b>	100	<b>100 x 100</b>	<b>78</b>
<b>SensL SPM</b>				
	<b>SPM-20</b>	848	<b>29 x 32</b>	<b>43</b>
	<b>SPM-50</b>	216	<b>59x 62</b>	<b>68</b>

# Determination of the operational voltage range of the SiPMs



**Measurements of  $V_{BD}$ , gain, DCR**

# Evolution of I<sub>reverse</sub> with the bias voltage

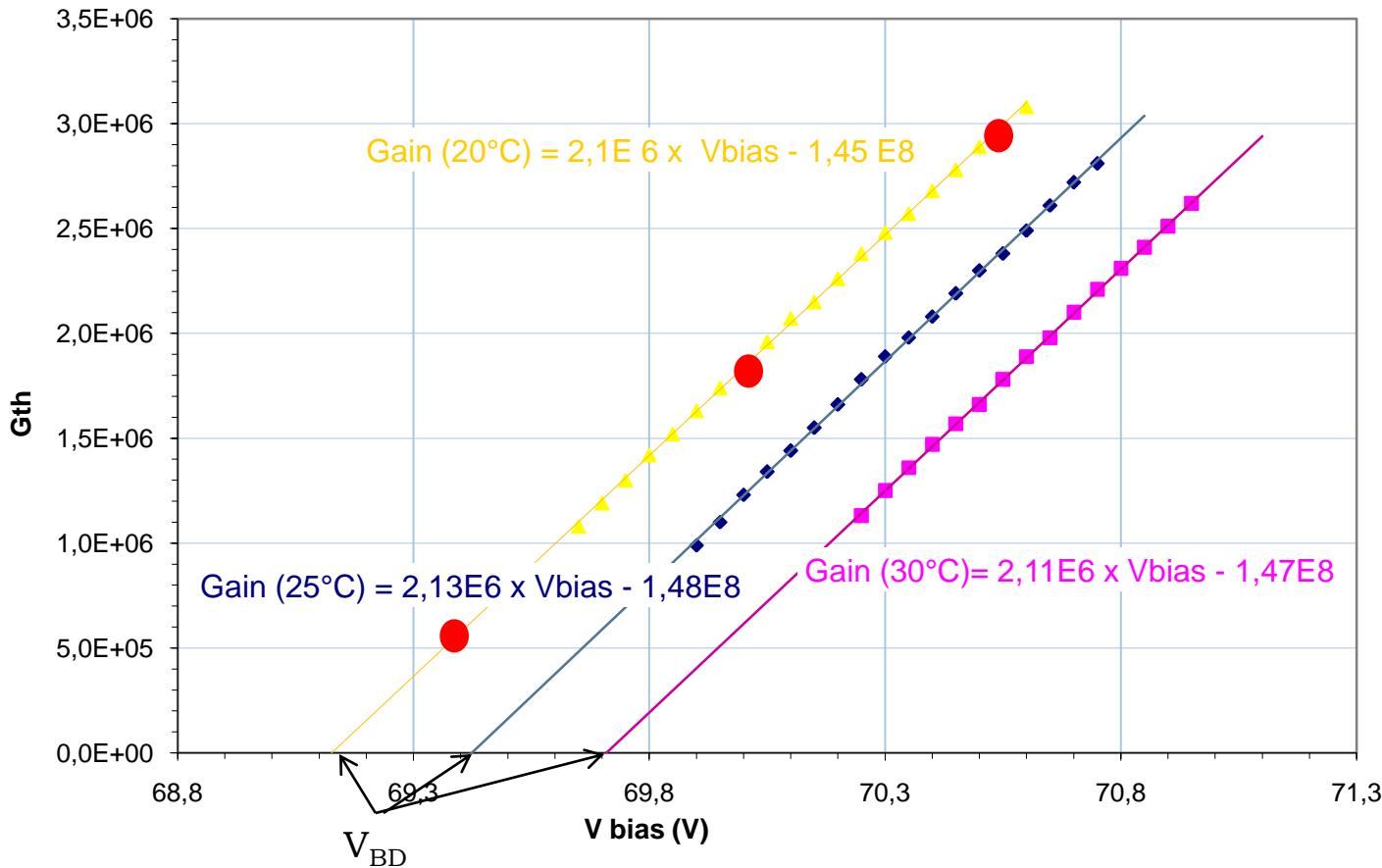


# Measurement of the gain and V<sub>BD</sub> (breakdown voltage)

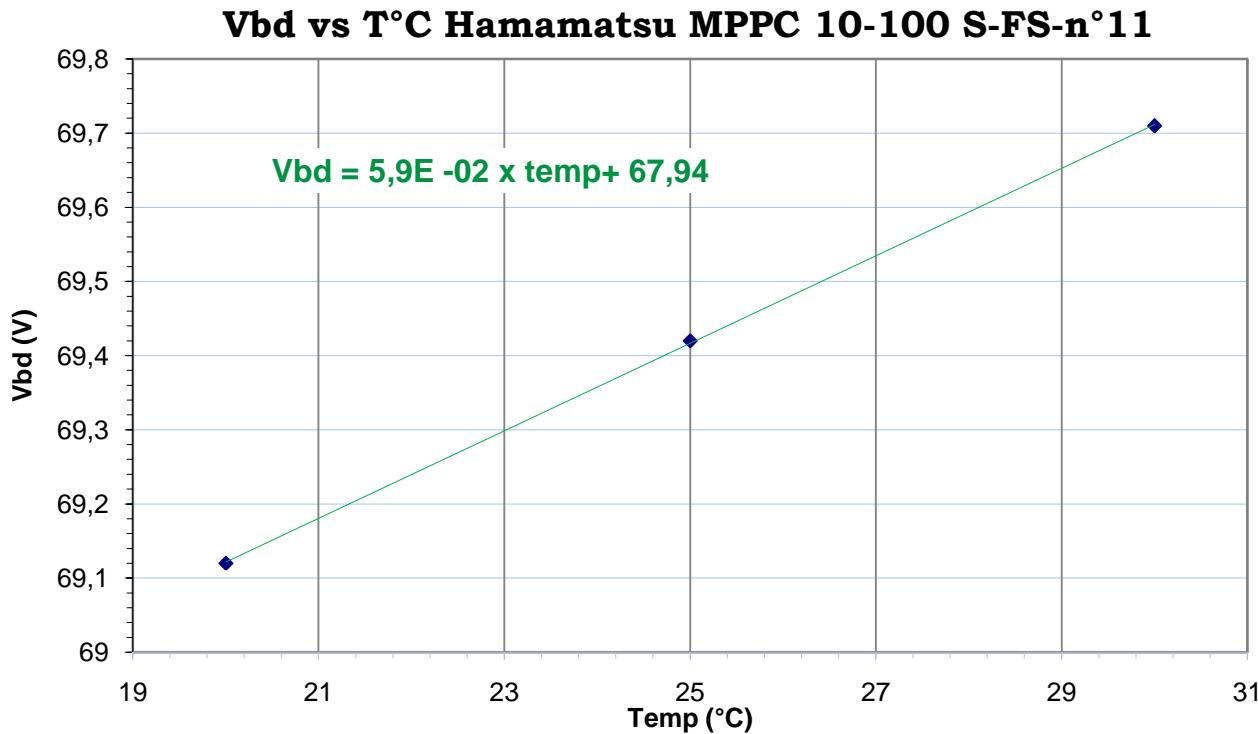
Defined as the charge developed in one pixel by a primary carrier

$$Gain = \frac{Q_{pixel}}{e} = \frac{C_{pixel} \times (Vbias - VBD)}{e}$$

**Gain MPPC 10-100S-FS-n°11**



# Evolution of V<sub>BD</sub> with temperature



Breakdown voltage increases with the temperature

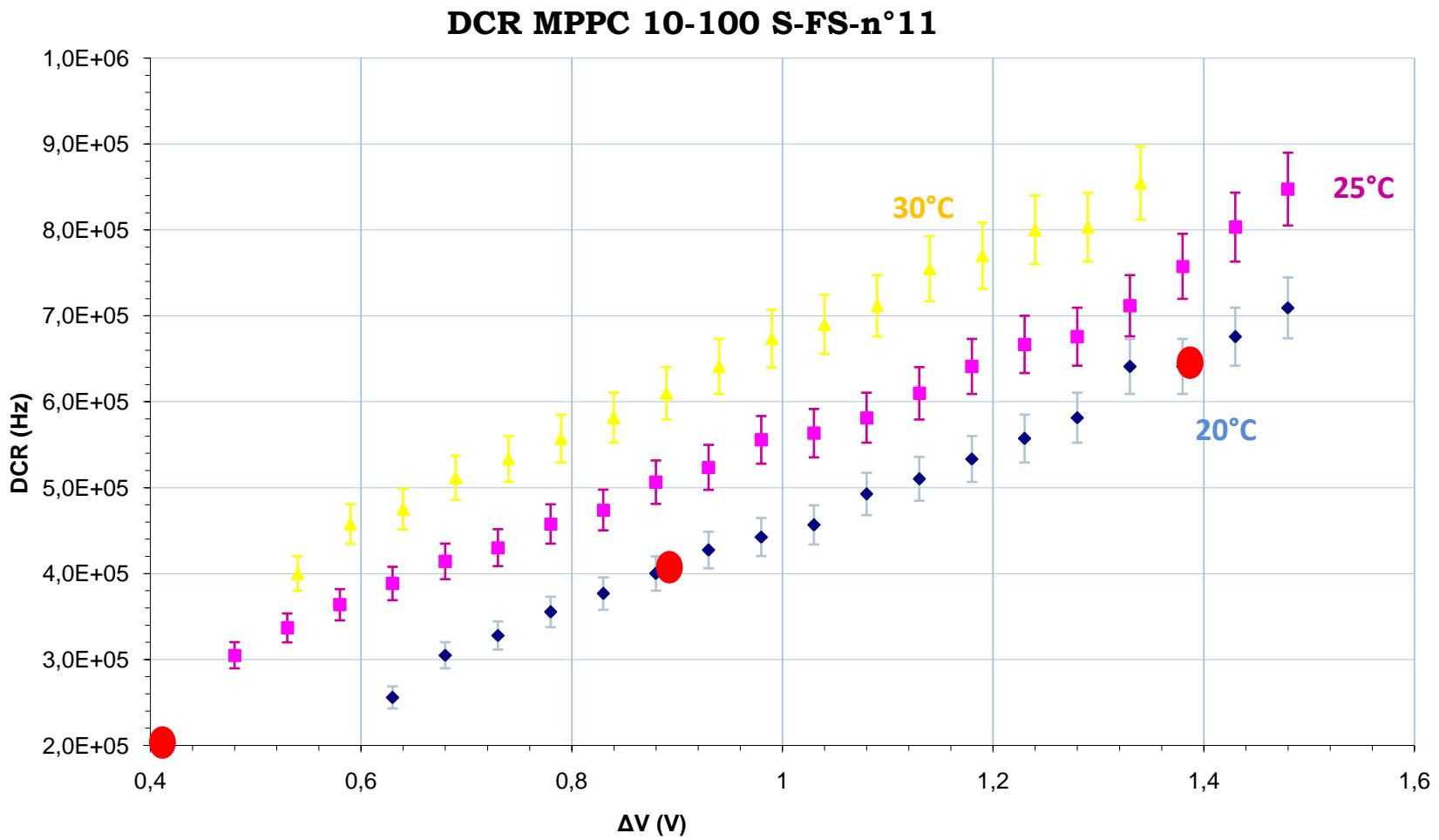


$dV_{BD}/dT \sim 59 \text{ mV/}^{\circ}\text{C}$  for the MPPC 10-100 S-FS

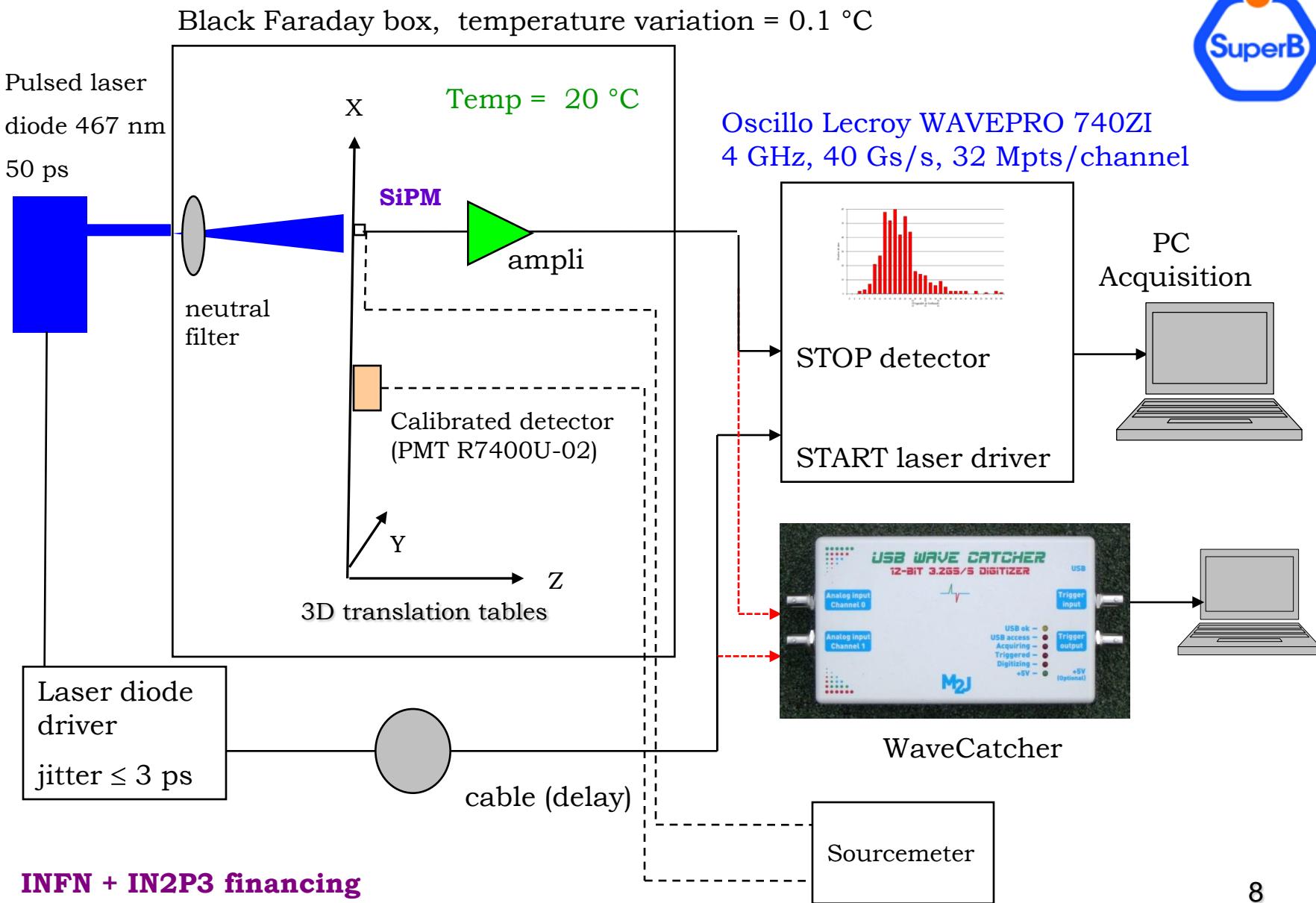
Correction of the bias voltage if the temperature changes inside the test bench to maintain a constant gain

# Measurement of the Dark Count Rate

Dark noise : thermally produced avalanches. Look the same as pulses from photon

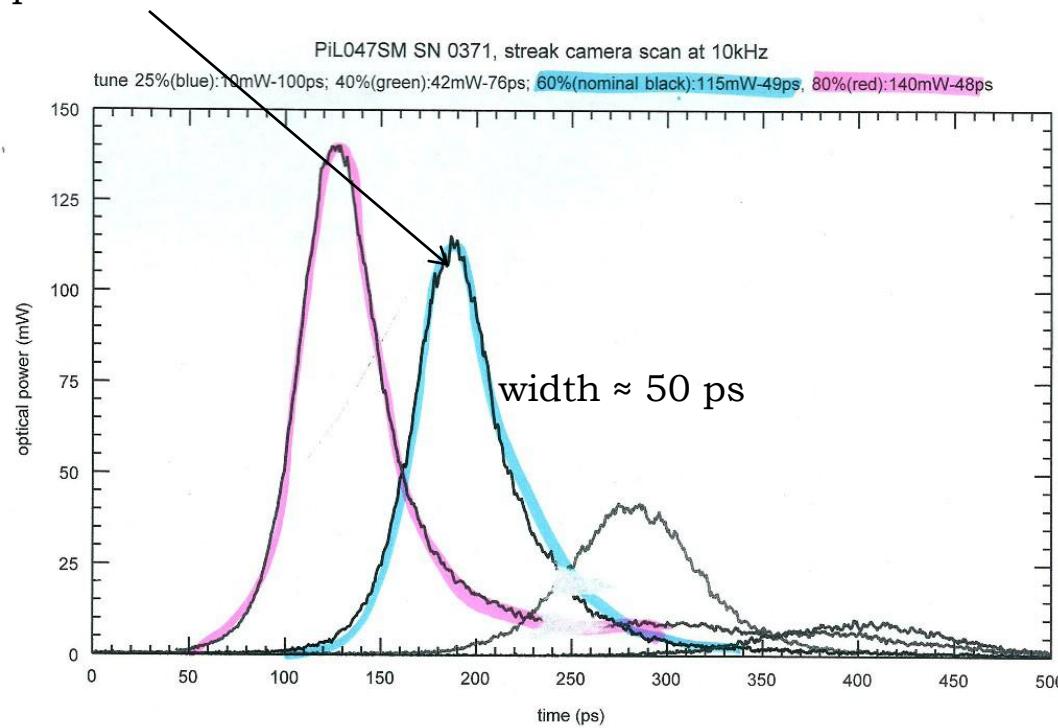


# Optical test bench for the TTS measurements



# Contribution to the timing resolution of the detection chain

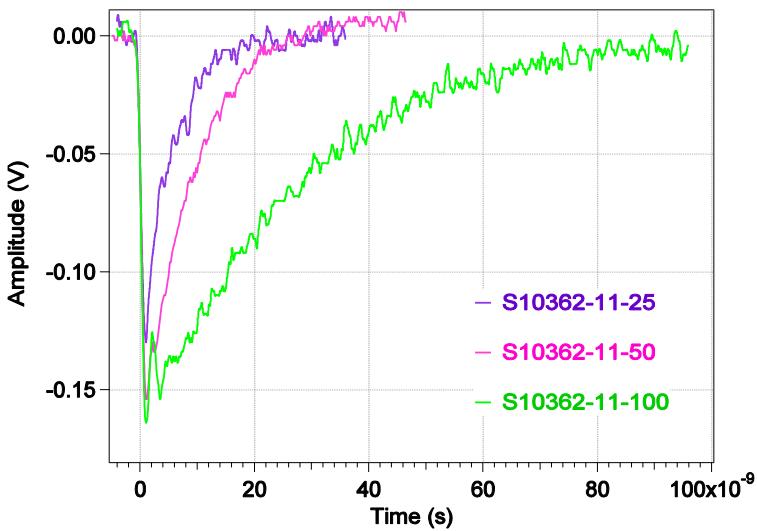
## Pilas pulsed laser diode



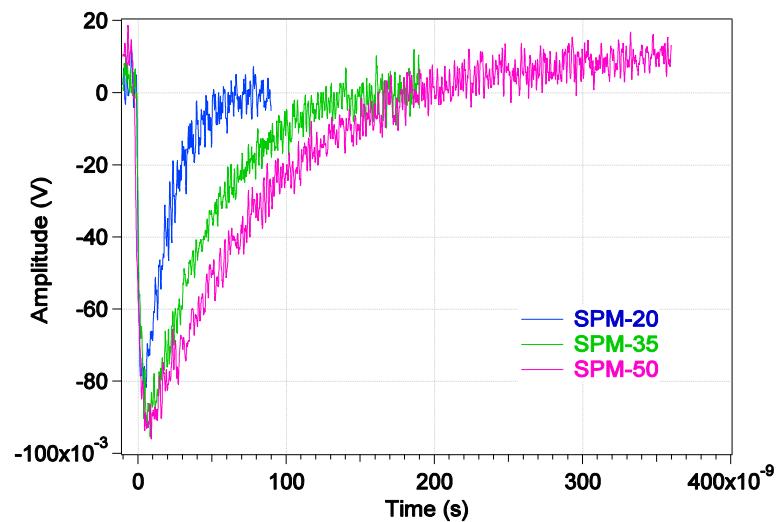
- Pilas driver : jitter  $\approx$  3 ps
- Timing resolution of the LECROY scope = 1 ps
- Timing resolution of the Wavecatcher = 8 ps
- Timing resolution of the SiPM ?

# SiPMs signals (voltage amplifier output)

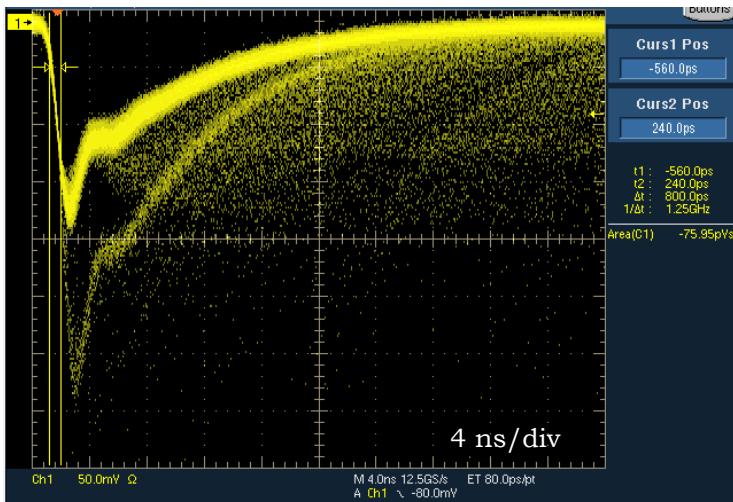
HAMAMATSU MPPC S10362-11



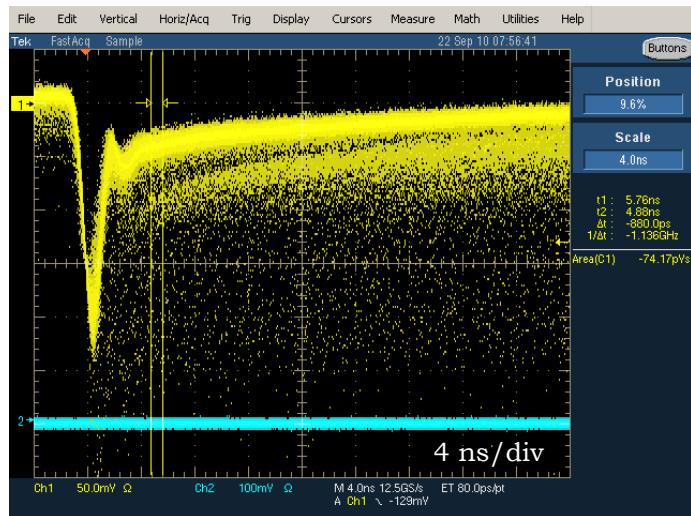
Sensl SPM



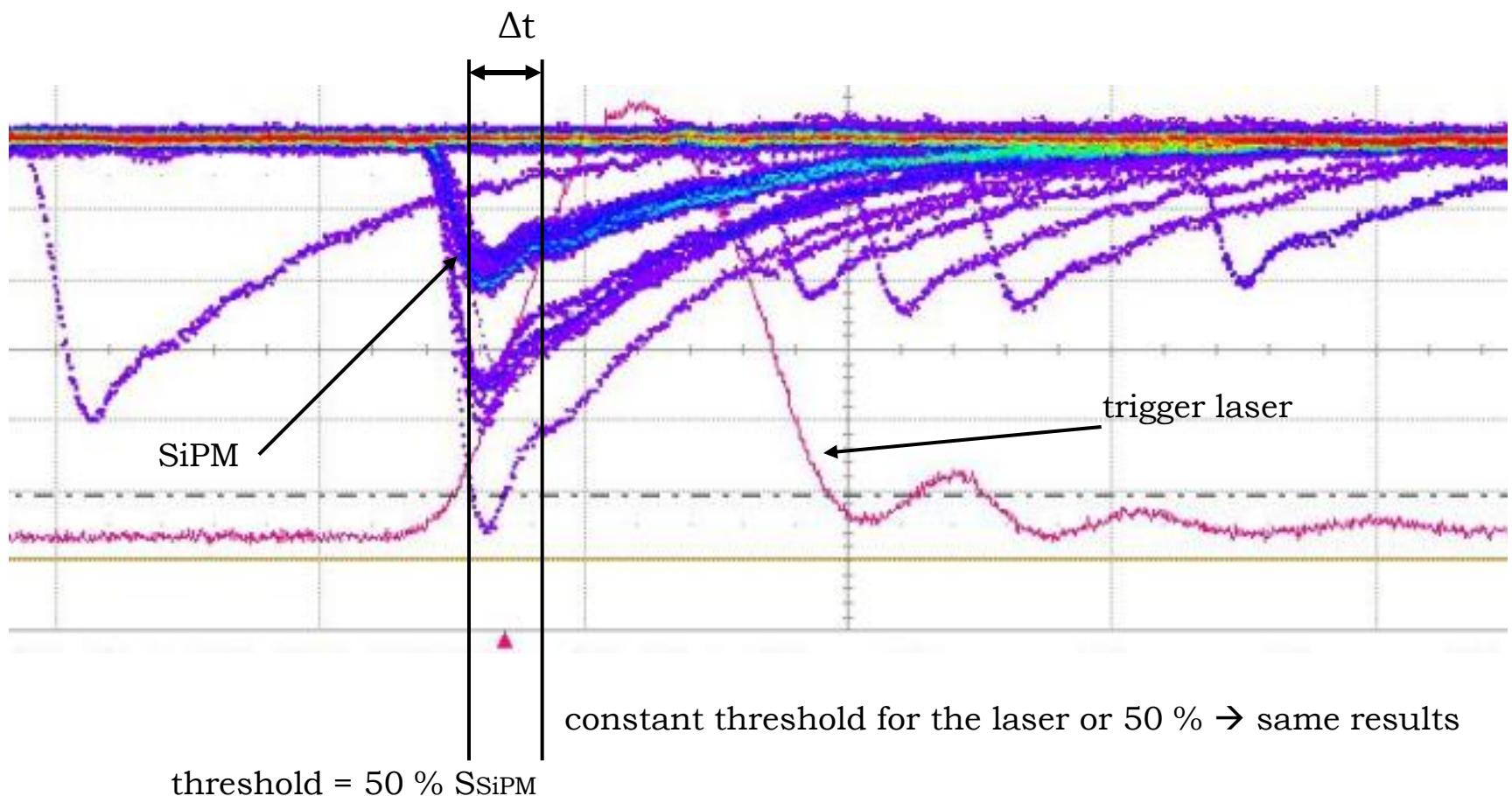
HAMAMATSU MPPC 50  $\mu\text{m}$  (2009)



FBK SiPM (ref B) (2009)



# Measurement principle of the SiPM timing resolution

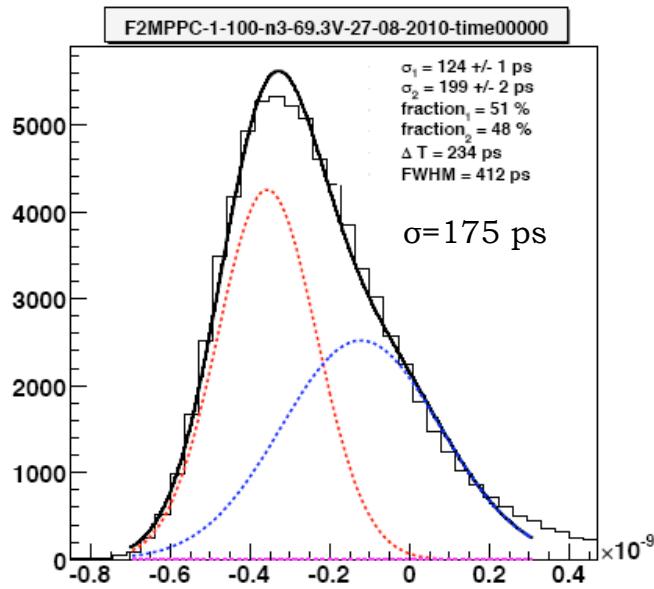


Measurement of the time between the laser and the SiPM signals → distribution of the  $\Delta t$

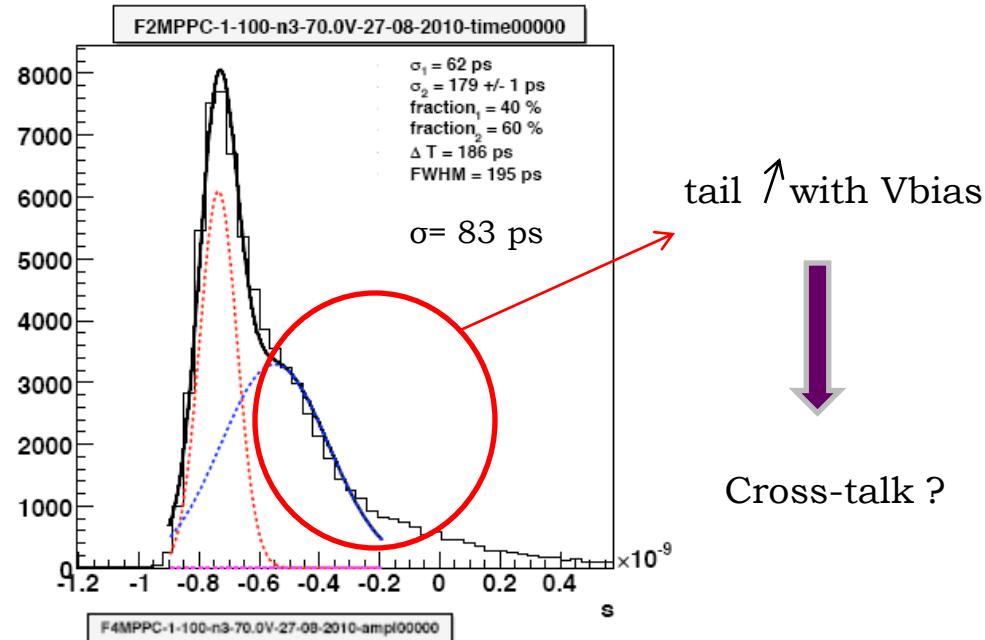
# $\Delta t$ and amplitude distribution of the SiPM signals

V. Puill, XIIth SuperB Project Meeting, Frascati, Sept 27-31 2010

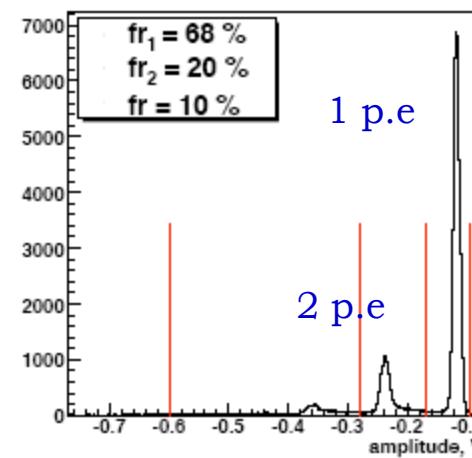
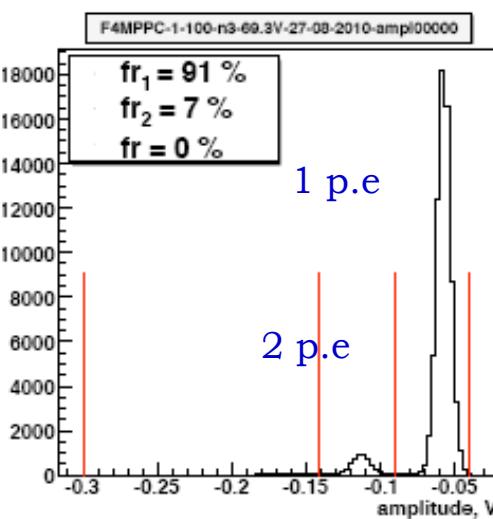
MPPC-1-100-n3-69.3V



MPPC-1-100-n3-70.0V

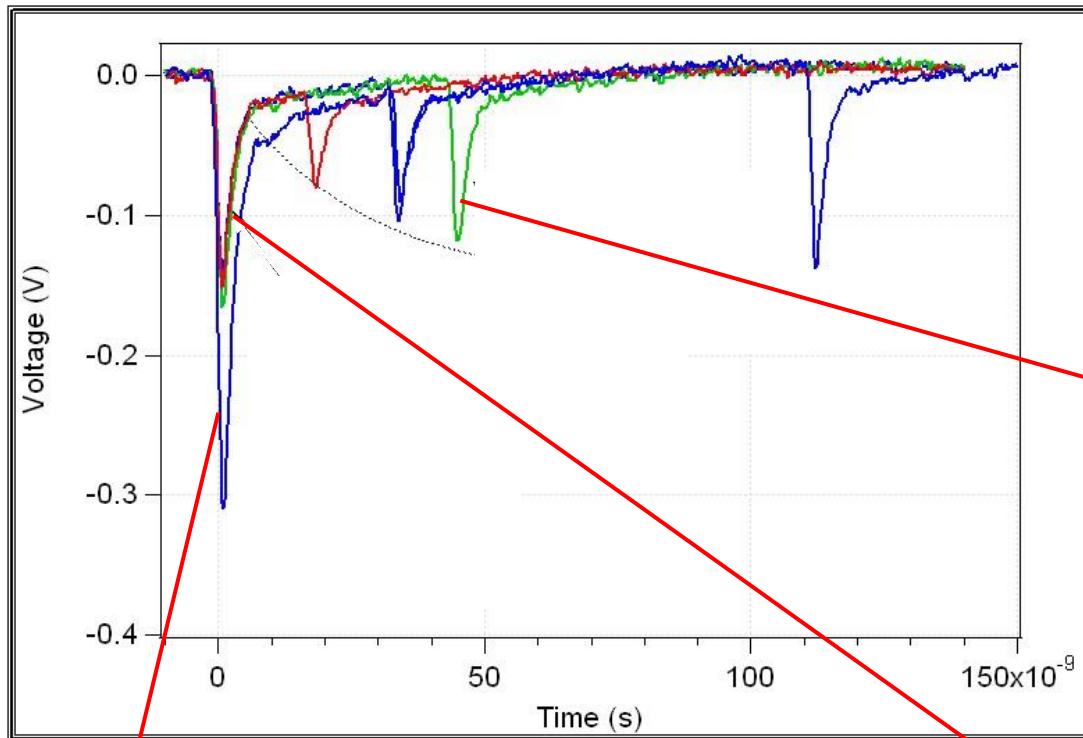


Data from LECROY oscilloscope



# Cross-talk definition

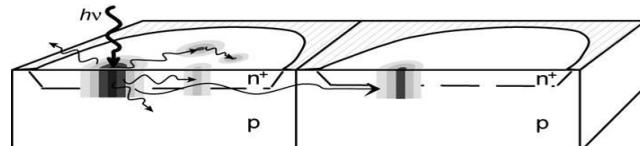
Noise : pulses triggered by non-photo-generated carriers



After-pulses

carriers trapped during the avalanche can produce delayed secondary pulses

Cross-talk

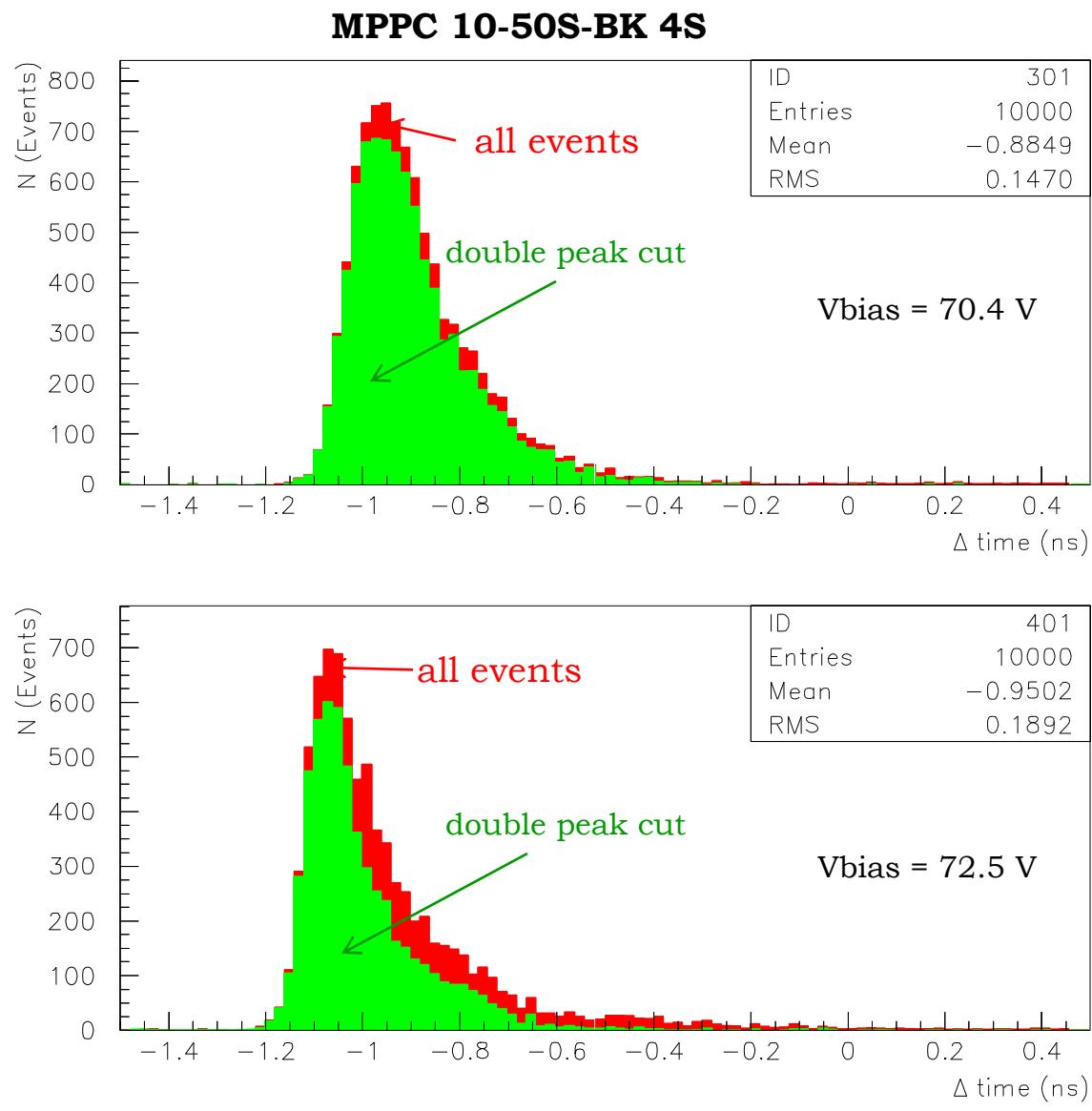


Dark noise

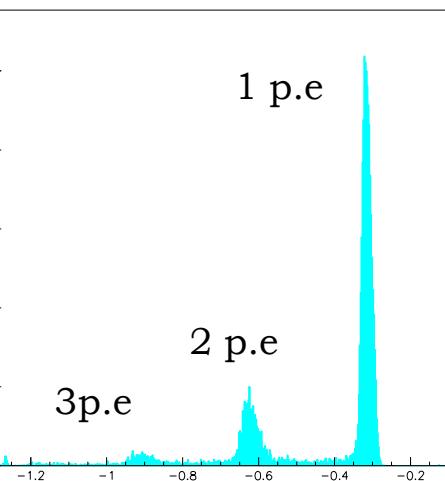
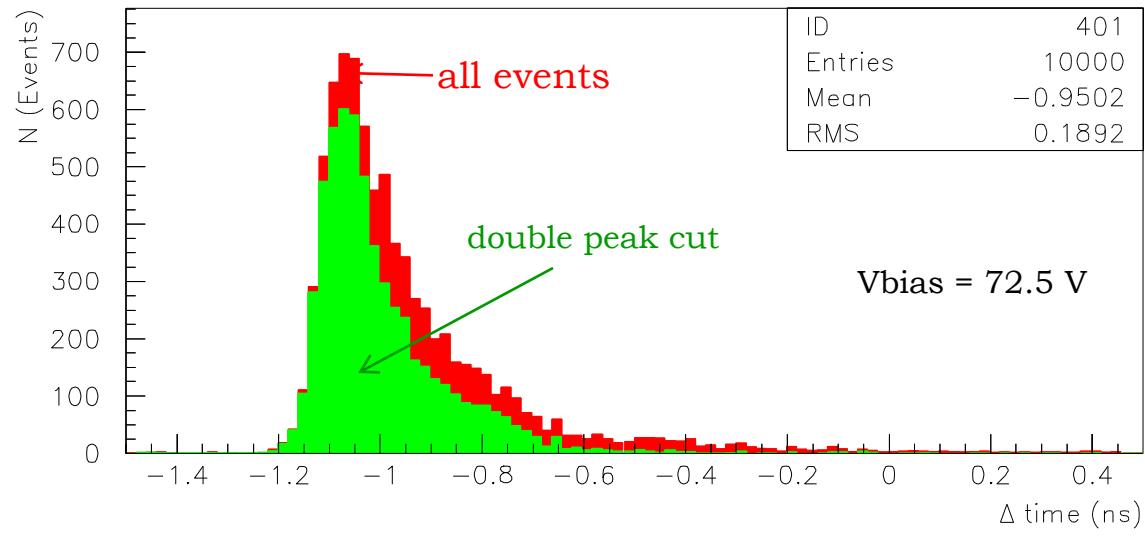
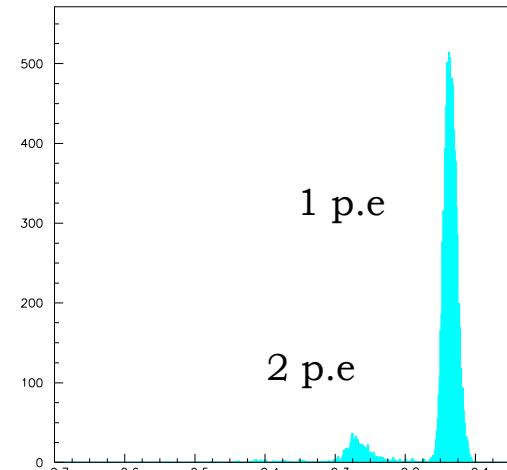
Thermally produced avalanche.  
Looks the same as pulse from photon

An avalanche in one pixel may produce an optical photon which can trigger another avalanche in a neighboring pixel without delay

# Contribution of the cross-talk to the TTS histo tail



Amplitude distribution  
Vbias = 70.4 V



Amplitude distribution  
Vbias = 72.5 V

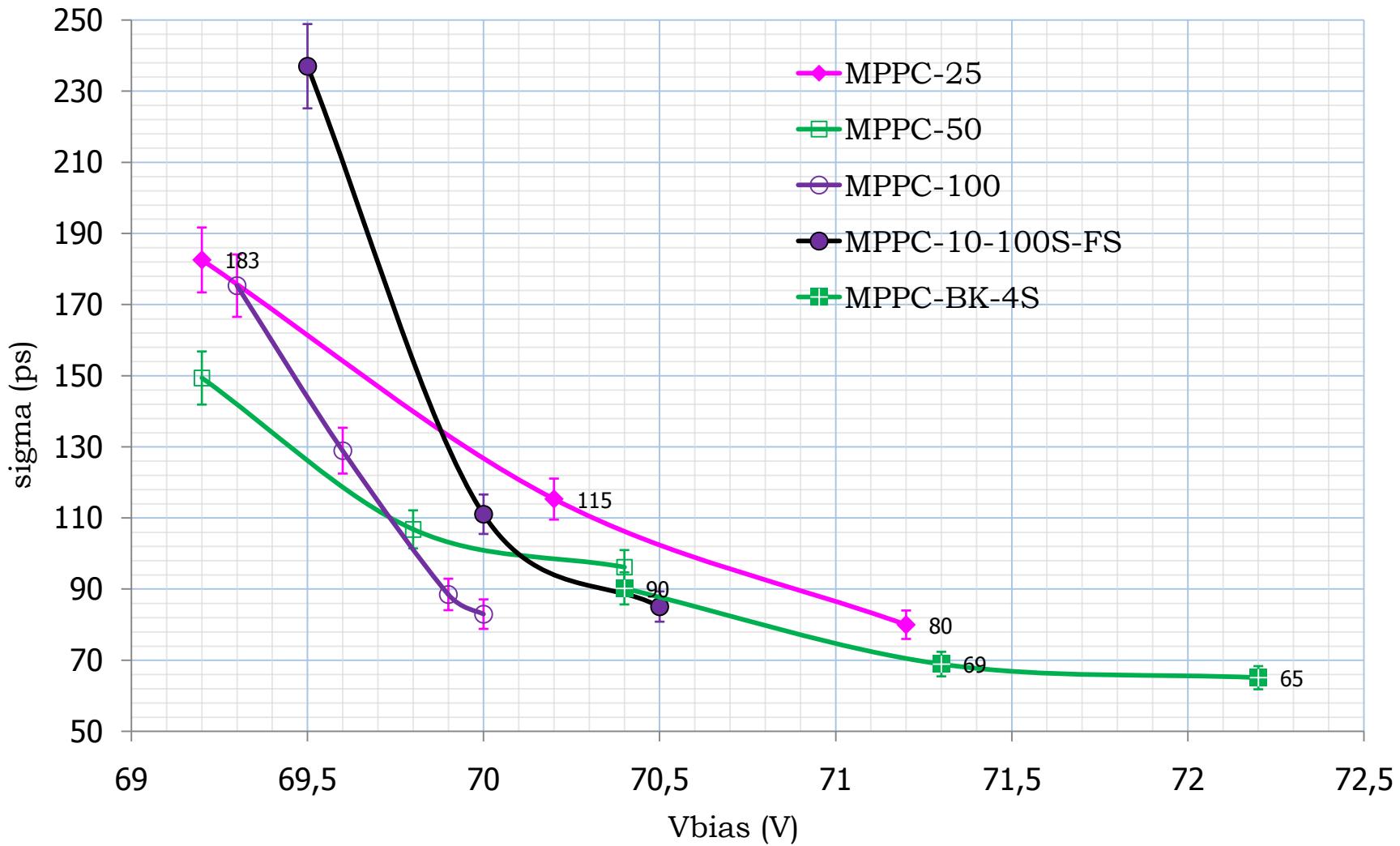


Tail : not only due to cross-talk

# Single Photo Electron Timing Resolution

HAMAMATSU devices

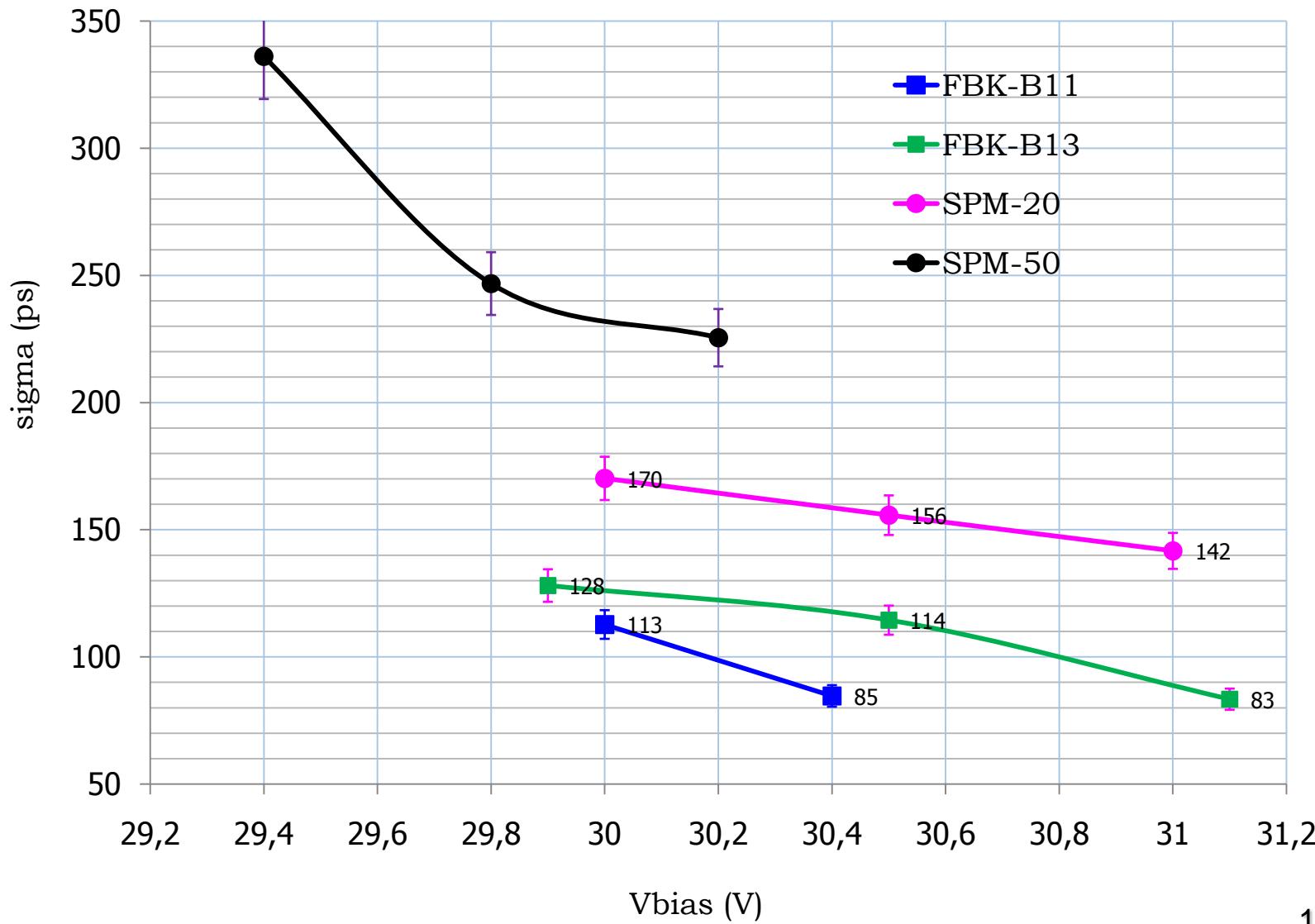
$T = 20 \text{ } ^\circ\text{C}$  ,  $\lambda = 467 \text{ nm}$



# Single Photo Electron Timing Resolution

FBK and Sensl devices

$T = 20 \text{ } ^\circ\text{C}$ ,  $\lambda = 467 \text{ nm}$



# Conclusion, further work

## Conclusion

- 65 ps < SPTR SiPM 1 mm<sup>2</sup> < 85 ps at 20 °C, 467 nm
- SPTR measurements with the Wavecatcher and the LECROY scope in agreement (15 %)
- Tail of the TTS histo → to be understood

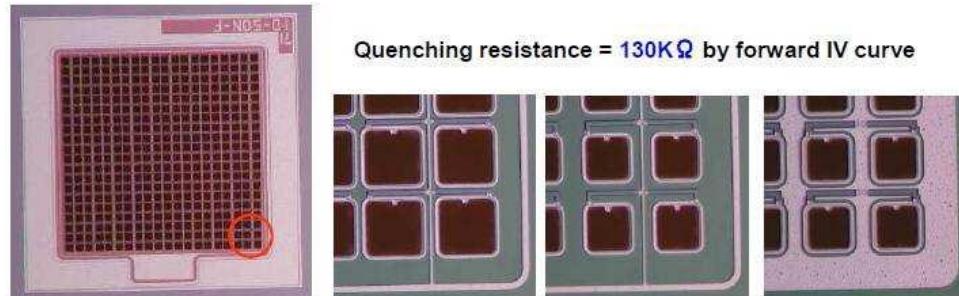
## Further work

- ★ **Measurement of the SiPM timing resolution of 9 mm<sup>2</sup> SiPM (HAMAMATSU, FBK, Sensl)**
- ★ **Measurement of the SiPM timing resolution in function of the :**
  - ❖ wavelength (403 nm and 633 nm)
  - ❖ simultaneous incident number of photons
  - ❖ temperature
- ★ **Study of Burle (64 anodes) and HAMAMATSU (SL10 4 and 16 anodes) MCP-PMTs**

# Additional slides

T = 20°C	type détecteur	Vbd (V)	V1 (V)	V2 (V)	V3 (V)
HPK	MPPC 10-50S-BK 4S n°10	69,1	70,1	70,9	71,5
DCR (Hz)	MPPC 10-50S-BK 4S n°10		2,91E+05	6,45E+05	1,18E+06
Gain th	MPPC 10-50S-BK 4S n°10		4,17E+05	7,56E+05	1,00E+06
HPK	MPPC 10-100S-FS n°11	69,12	69,5	70	70,5
DCR (Hz)	MPPC 10-100S-FS n°11		2,00E+05	4,00E+05	6,00E+05
Gain th	MPPC 10-100S-FS n°11		7,85E+05	1,85E+06	2,88E+06
HPK	S10362-11-025U-n°11	68,2	69,2	70,2	71,2
DCR (Hz)	S10362-11-025U-n°11		4,30E+04	1,08E+05	1,90E+05
Gain th	S10362-11-025U-n°11		1,28E+05	2,50E+05	3,74E+05
HPK	S10362-11-050U-n°3	68,35	69,2	69,8	70,4
DCR (Hz)	S10362-11-050U-n°3		1,53E+05	2,94E+05	4,81E+05
Gain th	S10362-11-050U-n°3		5,41E+05	9,24E+05	1,31E+06
HPK	S10362-11-100U-n°3	68,71	69,5	70	
DCR (Hz)	S10362-11-100U-n°3		1,76E+05	5,28E+05	
Gain th	S10362-11-100U-n°3		2,10E+06	3,36E+06	
FBK	FBK IRST B13	29,4	29,9	30,5	31,1
DCR (Hz)	FBK IRST B13			3,45E+06	5,87E+06
Gain th	FBK IRST B13		2,36E+05	5,19E+05	8,03E+05
FBK	FBK IRST B11	28,8	30	30,4	
DCR (Hz)	FBK IRST B11		2,95E+06	4,04E+06	
Gain th	FBK IRST B11		5,27E+05	7,18E+05	
SENSL	SensL 20μ	29,02	30	30,5	31
DCR (Hz)	SensL 20μ		7,09E+05	7,13E+05	7,61E+05
Gain th	SensL 20μ		4,53E+05	6,30E+05	8,13E+05

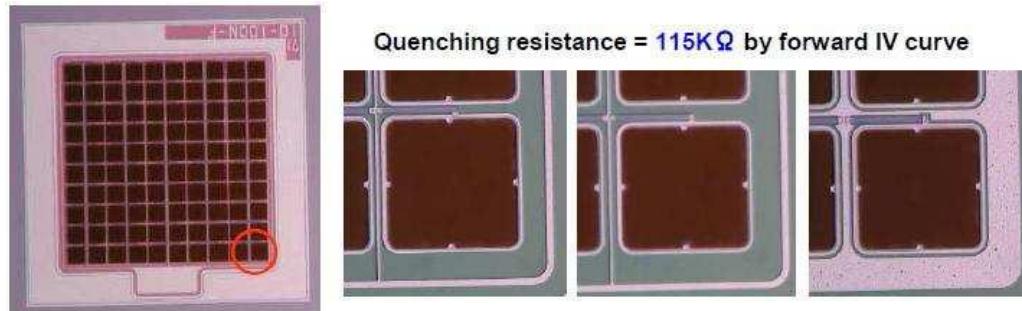
## MPPC 50 µm « wide trace »



Sample name	STD	Small pixel	Wide trace
Fill factor	62 %	38 %	38 %
$\Delta V(V_{op} - V_{br})$ #1	1.31 V	2.02 V	2.01 V
Dark count at $V_{op}$	535 Kcps	484 Kcps	502 Kcps
Pixel capacitance (Cd) #2	90 fF	59 fF	60 fF
Stray capacitance / pixel #3	2.5 fF	11 fF	23 fF
PDE at $V_{op}$ , 440nm	Not measure	Not measure	Not measure

#1 :  $V_{op}$  is at  $7.5 \times 10^5$    #2 : by GAIN vs VR curve   #3 :  $C_{total} / 400 - Cd$  at  $25^\circ\text{C}$

## MPPC 100 µm « wide trace »



Sample name	STD	Small pixel	Wide trace
Fill factor	78 %	72 %	72 %
$\Delta V(V_{op} - V_{br})$ #1	1.02 V	1.18 V	1.18 V
Dark count at $V_{op}$	1075 Kcps	1089 Kcps	1243 Kcps
Pixel capacitance (Cd) #2	373 fF	323 fF	325 fF
Stray capacitance / pixel #3	17 fF	37 fF	61 fF
PDE at $V_{op}$ , 440nm	79.7 %	76.2 %	77.6 %

#1 :  $V_{op}$  is at  $2.4 \times 10^6$    #2 : by GAIN vs VR curve   #3 :  $C_{total} / 100 - Cd$  at  $25^\circ\text{C}$